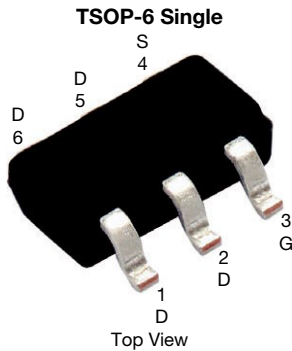


N-Channel 100 V (D-S) MOSFET

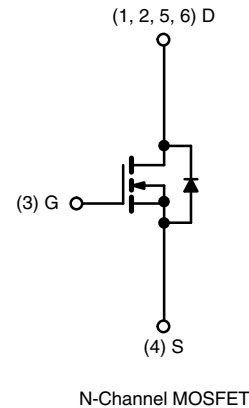


FEATURES

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available



| PRODUCT SUMMARY | |
|---|--------|
| V_{DS} (V) | 100 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V | 0.170 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 6$ V | 0.185 |
| Q_g typ. (nC) | 5.5 |
| I_D (A) | 2.4 |
| Configuration | Single |

| ORDERING INFORMATION | |
|---------------------------------|-----------------|
| Package | TSOP-6 |
| Lead (Pb)-free | Si3430DV-T1-E3 |
| Lead (Pb)-free and halogen-free | Si3430DV-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted) | | | | | |
|---|---------------|----------------|-------------|--------------|------|
| PARAMETER | | SYMBOL | 5 s | STEADY STATE | UNIT |
| Drain-source voltage | | V_{DS} | 100 | 100 | V |
| Gate-source voltage | | V_{GS} | ± 20 | ± 20 | |
| Continuous drain current ($T_J = 175$ °C) ^a | $T_A = 25$ °C | I_D | 2.4 | 1.8 | A |
| | $T_A = 85$ °C | | 1.7 | 1.3 | |
| Pulsed drain current | | I_{DM} | 8 | 8 | |
| Avalanche current | $L = 0.1$ mH | I_{AR} | 6 | 6 | |
| Repetitive avalanche energy (duty cycle ≤ 1 %) | | E_{AR} | 1.8 | 1.8 | mJ |
| Continuous source current (diode conduction) ^a | | I_S | 1.7 | 1 | A |
| Maximum power dissipation ^a | $T_A = 25$ °C | P_D | 2 | 1.14 | W |
| | $T_A = 85$ °C | | 1 | 0.59 | |
| Operating junction and storage temperature range | | T_J, T_{stg} | -55 to +150 | -55 to +150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|------------|---------|---------|------|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
| Maximum junction-to-ambient ^a | $t \leq 5$ s | R_{thJA} | 45 | 62.5 | °C/W |
| | Steady state | | 90 | 110 | |
| Maximum junction-to-foot (drain) | Steady state | R_{thJF} | 25 | 30 | |

Note

a. Surface mounted on 1" x 1" FR4 board



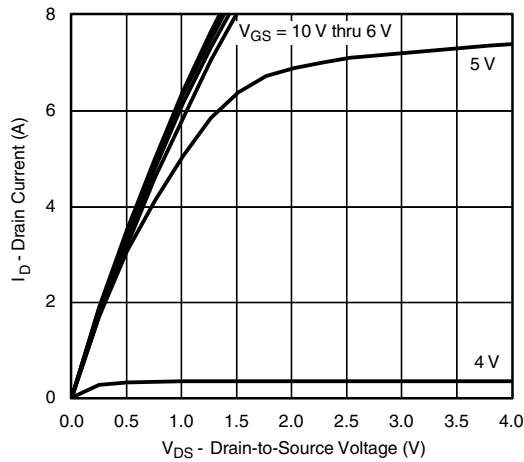
| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|---------------------|--|------|-------|-------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Gate threshold voltage | V _{GS(th)} | V _{DS} = V _{DS} , I _D = 250 μA | 2 | - | 4.2 | V |
| Gate-body leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = 80 V, V _{GS} = 0 V | - | - | 1 | μA |
| | | V _{DS} = 80 V, V _{GS} = 0 V, T _J = 85 °C | - | - | 25 | |
| On-state drain current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 8 | - | - | A |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D = 2.4 A | - | 0.148 | 0.170 | Ω |
| | | V _{GS} = 6 V, I _D = 2.3 A | - | 0.160 | 0.185 | |
| Forward transconductance ^a | g _{fs} | V _{DS} = 15 V, I _D = 2.4 A | - | 7 | - | S |
| Diode forward voltage ^a | V _{SD} | I _S = 1.7 A, V _{GS} = 0 V | - | 0.8 | 1.2 | V |
| Dynamic ^b | | | | | | |
| Total gate charge | Q _g | V _{DS} = 50 V, V _{GS} = 10 V, I _D = 2.4 A | - | 5.5 | 8.2 | nC |
| Gate-source charge | Q _{gs} | | - | 1.5 | - | |
| Gate-drain charge | Q _{gd} | | - | 1.4 | - | |
| Gate resistance | R _g | | 1 | - | 4 | Ω |
| Turn-on delay time | t _{d(on)} | V _{DD} = 50 V, R _L = 50 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω | - | 9 | 20 | ns |
| Rise time | t _r | | - | 11 | 20 | |
| Turn-off delay time | t _{d(off)} | | - | 16 | 30 | |
| Fall time | t _f | | - | 9 | 20 | |
| Gate resistance | R _g | V _{GS} = 0.1 V, f = 5 MHz | - | 2.8 | - | Ω |
| Source-drain reverse recovery time | t _{rr} | I _F = 1.7 A, di/dt = 100 A/μs | - | 50 | 80 | ns |

Notes

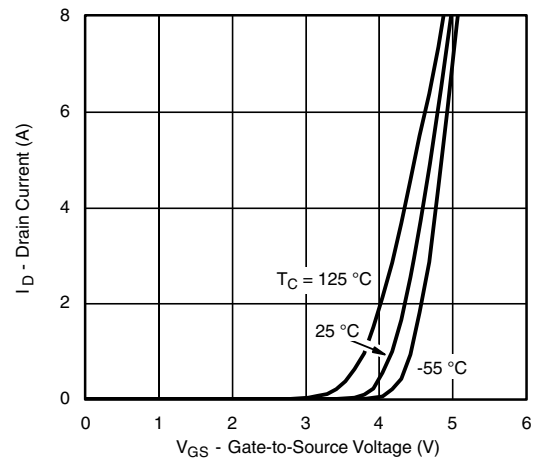
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

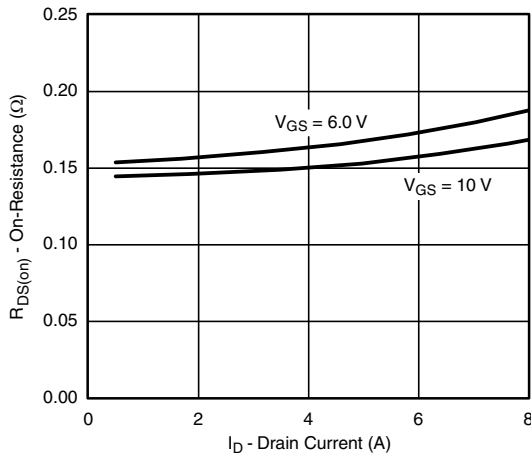
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



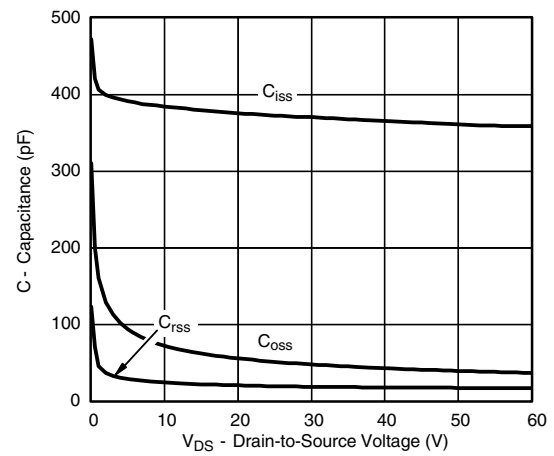
Output Characteristics



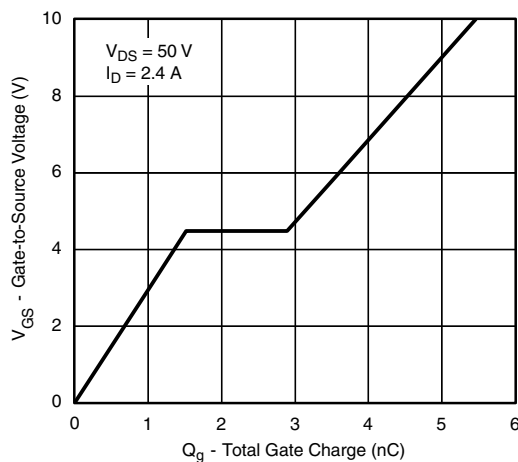
Transfer Characteristics



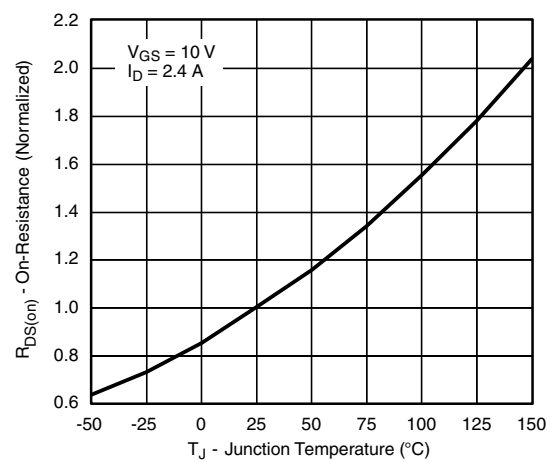
On-Resistance vs. Drain Current



Capacitance



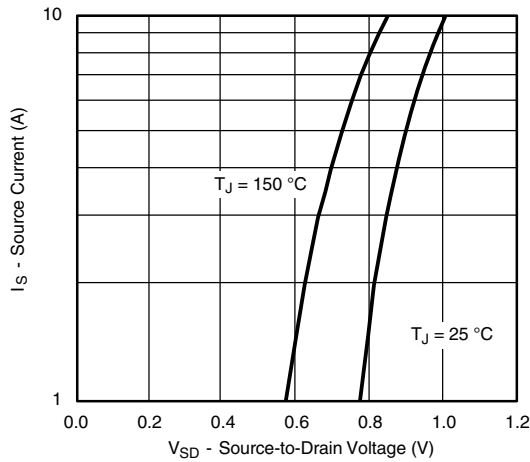
Gate Charge



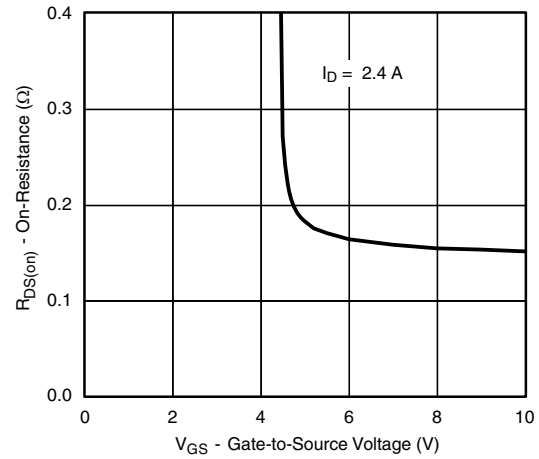
On-Resistance vs. Junction Temperature



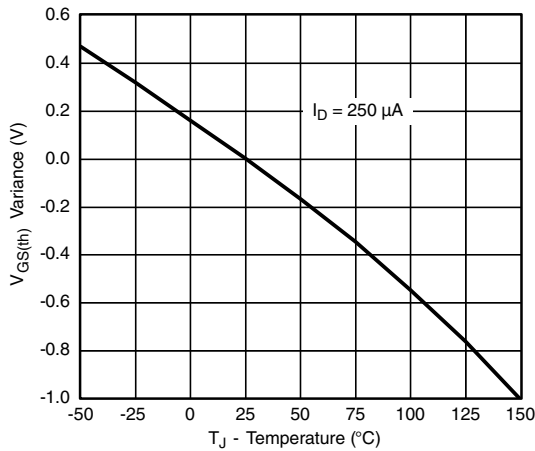
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



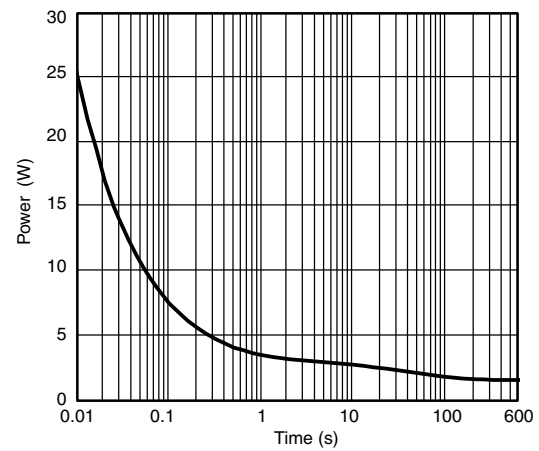
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



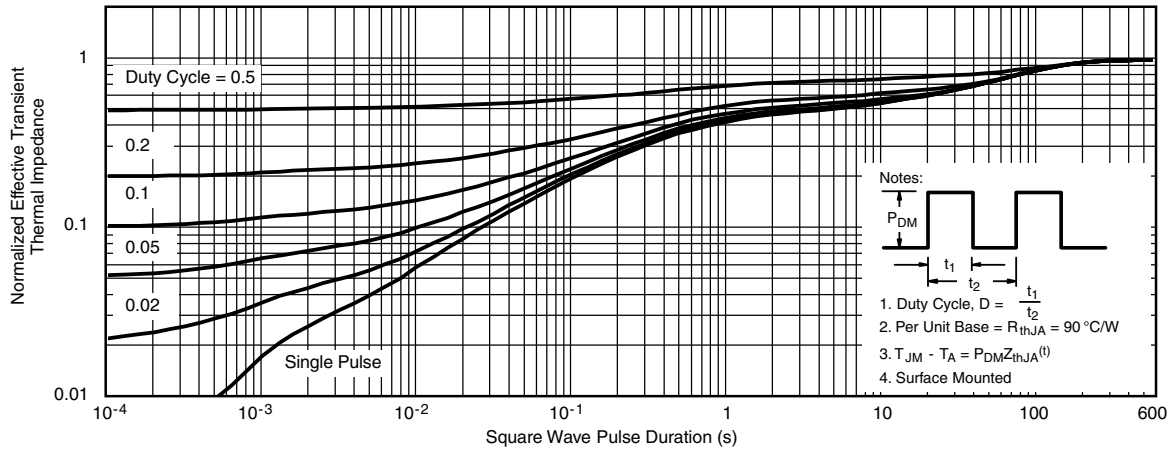
Threshold Voltage



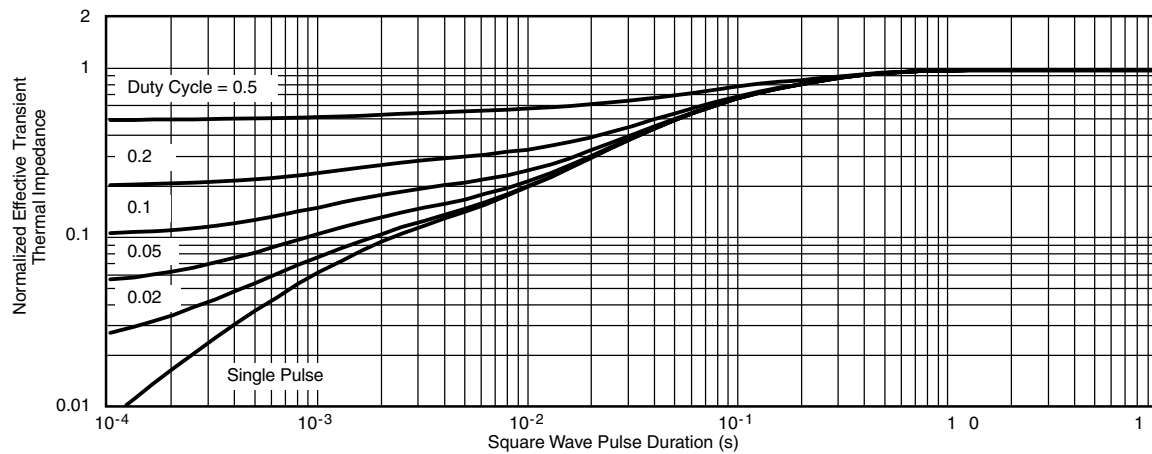
Single Pulse Power



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71235.



TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP



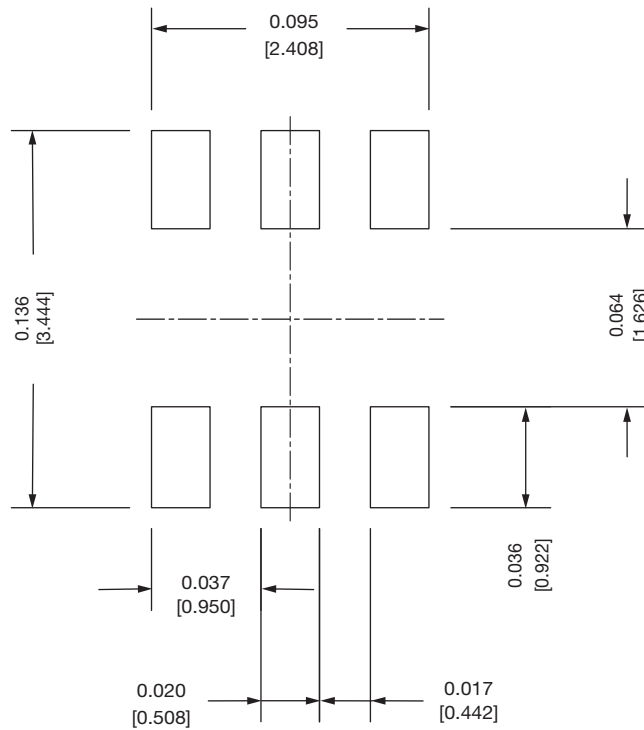
6-LEAD TSOP



| Dim | MILLIMETERS | | | INCHES | | |
|--------------------------------|-------------|------|------|------------|-------|-------|
| | Min | Nom | Max | Min | Nom | Max |
| A | 0.91 | - | 1.10 | 0.036 | - | 0.043 |
| A ₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 |
| A ₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 |
| c | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 |
| E | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 |
| E ₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 |
| e | 0.95 BSC | | | 0.0374 BSC | | |
| e ₁ | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 |
| L ₁ | 0.60 Ref | | | 0.024 Ref | | |
| L ₂ | 0.25 BSC | | | 0.010 BSC | | |
| R | 0.10 | - | - | 0.004 | - | - |
| θ | 0° | 4° | 8° | 0° | 4° | 8° |
| θ ₁ | 7° Nom | | | 7° Nom | | |
| ECN: C-06593-Rev. I, 18-Dec-06 | | | | | | |
| DWG: 5540 | | | | | | |



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
 DWG: 3010



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